

March 2011

FDZ1905PZ

Common Drain P-Channel 1.5V PowerTrench® WL-CSP MOSFET -20V, -3A, $123m\Omega$

Features

- Max $r_{S1S2(on)} = 126m\Omega$ at $V_{GS} = -4.5V$, $I_{S1S2} = -1A$
- Max $r_{S1S2(on)} = 141 m\Omega$ at $V_{GS} = -2.5 V$, $I_{S1S2} = -1 A$
- Max $r_{S1S2(on)} = 198m\Omega$ at $V_{GS} = -1.8V$, $I_{S1S2} = -1A$
- Max $r_{S1S2(on)} = 303m\Omega$ at $V_{GS} = -1.5V$, $I_{S1S2} = -1A$
- Occupies only 1.5 mm² of PCB area, less than 50% of the area of 2 x 2 BGA
- Ultra-thin package: less than 0.65 mm height when mounted to PCB
- High power and current handling capability
- HBM ESD protection level > 4kV (Note 3)
- RoHS Compliant

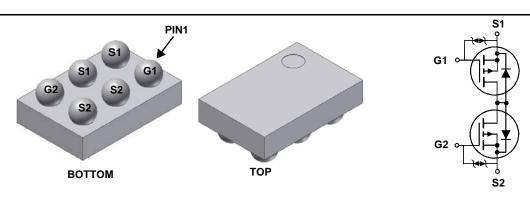


General Description

This device is designed specifically as a single package solution for the battery charge switch in cellular handset and other ultra-portable applications. It features two common drain P-channel MOSFETs, which enables bidirectional current flow, on Fairchild's advanced 1.5V PowerTrench® process with state of the art "low pitch" WL-CSP packaging process, the FDZ1905PZ minimizes both PCB space and $r_{S1S2(on)}$. This advanced WL-CSP MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, ultra-low profile packaging, low gate charge, and low $r_{S1S2(on)}$.

Applications

- Battery management
- Load switch
- Battery protection



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units	
V _{S1S2}	Source1 to Source2 Voltage			-20	V	
V_{GS}	Gate to Source Voltage			±8	V	
I _{S1S2}	Source1 to Source2 Current -Continu	uous T _A = 25°C	(Note 1a)	-3	^	
	-Pulsed			- 15	Α	
P _D	Power Dissipation (Steady State)	T _A = 25°C	(Note 1a)	1.5	W	
	Power Dissipation $T_A = 25^{\circ}C$ (Note 1b)			0.9	VV	
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C	

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	83	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	140	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package Reel Size		Tape Width	Quantity
5	FDZ1905PZ	WL-CSP 1.0X1.5	7"	8mm	5000 units

Electrical Characteristics $T_J = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	Off Characteristics					
I _{S1S2}	Zero Gate Voltage Source1 to Source2 Current	$V_{S1S2} = -16V, V_{GS} = 0V$			-1	μА
I _{GSS}	Gate Body Leakage Current	$V_{GS} = \pm 8V, V_{S1S2} = 0V$			±10	uA

On Characteristics (Note 2)

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{S1S2}, I_{S1S2} = -250 \mu A$	-0.4	-0.7	-1.0	V
r _{S1S2(on)}	Static Source1 to Source2 On Resistance	$V_{GS} = -4.5V$, $I_{S1S2} = -1A$		99	126	mΩ
		$V_{GS} = -2.5V$, $I_{S1S2} = -1A$		112	141	
		$V_{GS} = -1.8V$, $I_{S1S2} = -1A$		132	198	
		$V_{GS} = -1.5V$, $I_{S1S2} = -1A$		164	303	11152
		$V_{GS} = -4.5V$, $I_{S1S2} = -1A$, $T_J = 125$ °C		135	195	
9 _{FS}	Forward Transconductance	$V_{S1S2} = -5V, I_{S1S2} = -1A$		8		S

Switching Characteristics (Note 2)

t _{d(on)}	Turn-On Delay Time		12	22	ns
t _r	Rise Time	$V_{S1S2} = -10V, I_{S1S2} = -1A$	36	58	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = -4.5V$, $R_{GEN} = 6\Omega$	143	229	ns
t _f	Fall Time		182	291	ns

Notes:1. $R_{\theta,JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta,JC}$ is guaranteed by design while $R_{\theta,CA}$ is determined by the user's board design.



a. 83°C/W when mounted on a 1 in² pad of 2 oz copper



b.140°C/W when mounted on a minimum pad of 2 oz copper

- 2. Pulse Test: Pulse Width < 300ms, Duty cycle < 2.0%.
- 3. The diode connected between the gate and source serves only protection against ESD. No gate overvoltage rating is implied.

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Typical Characteristics T_J = 25°C unless otherwise noted

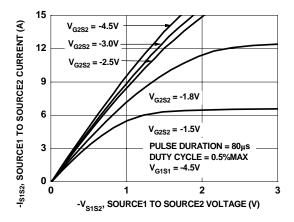
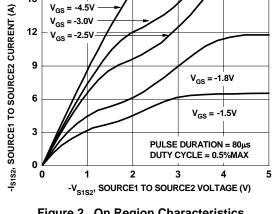


Figure 1. On Region Characteristics



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Figure 2. On Region Characteristics

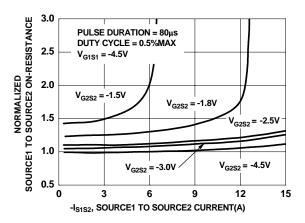


Figure 3. Normalized On-Resistance vs Drain Current and Gate Voltage

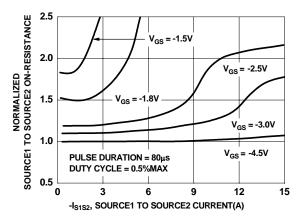


Figure 4. Normalized On-Resistance vs Drain Current and Gate Voltage

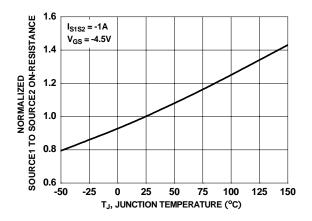


Figure 5. Normalized On Resistance vs Junction Temperature

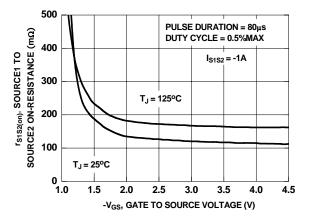


Figure 6. On-Resistance vs Gate to Source Voltage

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Typical Characteristics T_J = 25°C unless otherwise noted

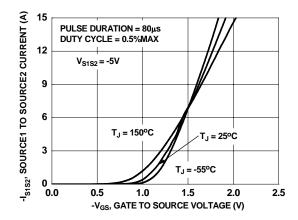


Figure 7. Transfer Characteristics

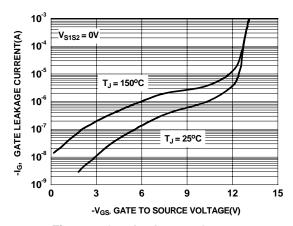


Figure 8. Gate Leakage vs Gate to Source Voltage

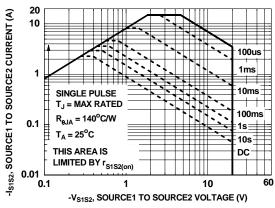


Figure 9. Forward Bias Safe Operating Area

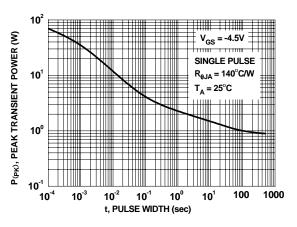


Figure 10. Single Pulse Maximum Power Dissipation

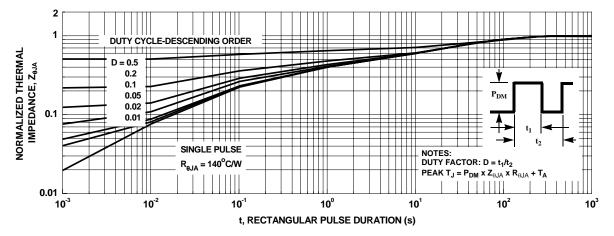
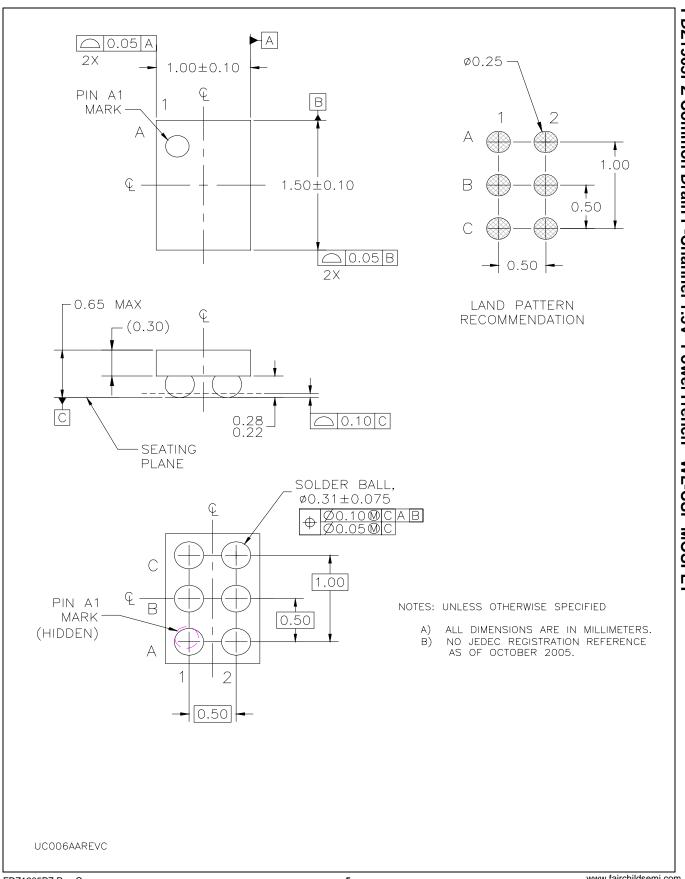


Figure 11. Transient Thermal Response Curve

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